

P-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}$ (m Ω)(TYP.)	I _D (A) ^{a, e}	Q _g (Typ.)			
-60	12 at V _{GS} = -10V	60	121 nC			
-00	20 at V _{GS} = -4.5 V	-60				

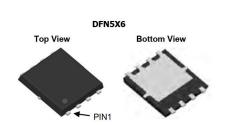
FEATURES

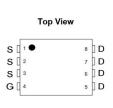
- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested

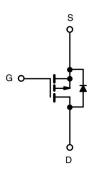
APPLICATIONS

- Notebook
 - Load Switch









P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	Limit	UNIT	
Drain-Source Voltage		V _{DS}	-60		
Gate-Source Voltage		V _{GS}	±20	V	
Continuous Drain Current /T 150 °C) 3	T _A = 25 °C	1	-60		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C	l _D	-50		
Pulsed Drain Current		I _{DM}	-240	Α	
Continuous Source Current (Diode Conduction) ^a		Is	-60		
Avalanche Current	L = 0.1 mH	I _{AS}	-62		
Single Pulse Avalanche Energy		E _{AS}	225	mJ	
Maximum Power Dissipation ^a	T _A = 25 °C	D	43	w	
	T _A = 70 °C	P _D	38		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +150	°C	
Soldering Recommendations (Peak Temperature) b, c			260		

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT	
Maximum Junction-to-Ambient a	t ≤ 10 s	R _{thJA}	15	23	°C/W	
Maximum Junction-to-Ambient *	Steady State		22	35		
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	1	1.3		

Notes

- a. Surface mounted on 1" x 1" FR4 board.
- b. The DFN5x6 is a lead less package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure a dequate bottom side solder interconnection.
- c. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.



PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-1	-	-3	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	±100	nA	
7 0	I _{DSS}	$V_{DS} = -48 \text{ V}, V_{GS} = 0 \text{ V}$	=	.=	-1	μА	
Zero Gate Voltage Drain Current		$V_{DS} = -48 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 70 ^{\circ}\text{C}$	-	-	-10		
On-State Drain Current a	I _{D(on)}	$V_{DS} \le -5 V$, $V_{GS} = -10 V$	-60	-	-	Α	
Drain-Source On-State Resistance a	R _{DS(on)}	$V_{GS} = -10 \text{ V}, I_D = -15 \text{ A}$	=	12	14.5	mO	
Diani-Source On-State Resistance		$V_{GS} = -4.5 \text{ V}, I_D = -10 \text{ A}$	-	20	25	mΩ	
Forward Transconductance ^a	9 _{fs}	$V_{DS} = -15 \text{ V}, I_{D} = -15 \text{ A}$	=	31	-	S	
Diode Forward Voltage ^a	V_{SD}	$I_S = -1 A, V_{GS} = 0 V$	-	-	-1	V	
Dynamic ^b							
Input Capacitance	C _{iss}		-	9360	-	pF	
Output Capacitance	Coss	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}, f=1 \text{ MHz}$	-	368	-		
Reverse Transfer Capacitance	C _{rss}		-	300	-		
Total Gate Charge	Q_g		=	121	190	nC	
Gate-Source Charge	Q _{gs}	$V_{DS} = -30 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -15 \text{ A}$	-	20	-		
Gate-Drain Charge	Q_{gd}		-	32	-		
Gate Resistance	R_g		-	3.5	-	Ω	
Turn-On Delay Time	t _{d(on)}		-	20	-		
Rise Time	t _r	V_{DD} = -30 V, R_L = 30 Ω		20	-		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong -15 \text{ A}, V_{GEN} = -10 \text{ V}, R_g = 6 \Omega$	-	205	-	ns	
Fall Time	t _f		-	90	E		
Source-Drain Reverse Recovery Time	t _{rr}	$I_F = -4.5 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}$	-	45	-		
Drain-Source Body Diode Characteristic	:s						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			- 60	Α	
Pulse Diode Forward Current	I _{SM}				- 240	_ ^	
Body Diode Voltage	V _{SD}	I _S = -1 A, V _{GS} = 0 V		- 0.6	- 1	V	
Body Diode Reverse Recovery Time	t _{rr}			39		nS	
Body Diode Reverse Recovery Charge	Q _{rr}			40		nC	
Reverse Recovery Fall Time	t _a	I _F = 15 A, dl/dt = 100 A/μs, T _J = 25 °C		19			
Reverse Recovery Rise Time	t _b			25		nS	

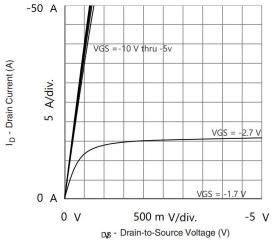
Notes

- a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %. b. Guaranteed by design, not subject to production testing.

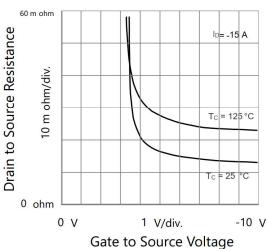
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



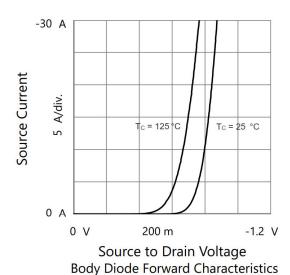
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



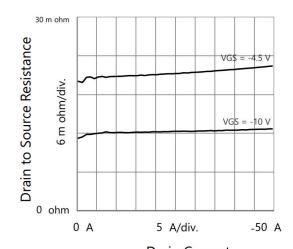




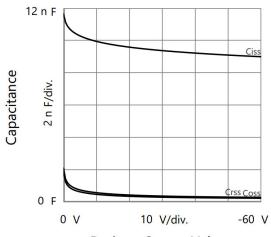
Drain to Source Resistance vs. Gate to Source Voltage



Gate to Source Voltage Transfer Characteristics



Drain Current
Drain to Source Resistance vs. Drain Current



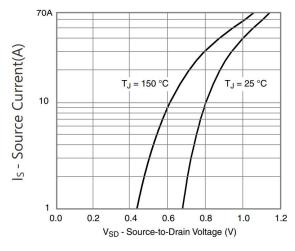
Drain to Source Voltage Capacitances

125



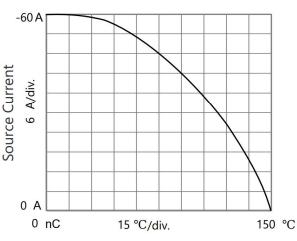


TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



10 $V_{DS} = -30 \text{ V}$ $I_{D} = -15 \text{ A}$ V_{GS} - Gate-to-Source (V) 8 6 4 2 0 0 25 70 100 Qg - Total Gate Charge (nC)

Source-Drain Diode Forward Voltage



50 W Power Dissipation (W) W/div. 0 W 150 °C 15 °C/div. 0 nC

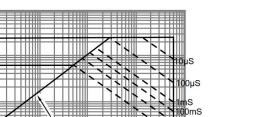
 $T_{C} \textbf{-} \textbf{Case Temperature}_{\text{Power Derating}}$

Gate Charge

T_C - Case Temperature

Current Derating

-1000A

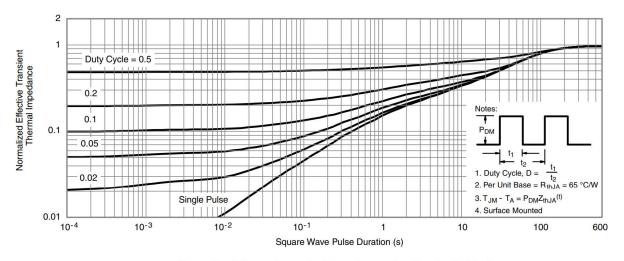


Source Current decade/div. limited by Ros(ON -0.1A -0.01 V decade/div. -100V

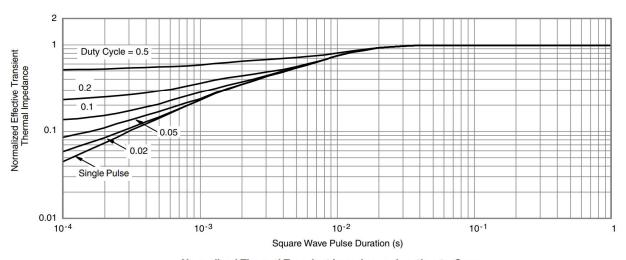
Source to Drain Voltage Safe Operating Area, Junction-to-Ambient



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case





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